

Appl. No. 10/694,684  
Response dated 08/29/2005  
Reply to Office Action 06/01/2005

Attorney Docket No.: TS02-1193  
N1085-90160

**Amendments to the Specification:**

Please amend the paragraph that follows the heading "Formation of Trench Openings 56,58 – Fig. 10" on page 11 of the specification according to the following amended paragraph:

As shown in Fig. 10, using photoresist capacitance trench masking portion 43 as a mask, the exposed portions 70, 72 of the patterned capacitance dielectric layer 32' between the respective initial via openings 36, 38 and the capacitance trench masking portion 43, the underlying twice patterned ARC 18" and the underlying twice patterned oxide layer 16" are etched down to a depth substantially equal to the bottom of the capacitance trench 25 to form respective trench openings 56, 58 contiguous and continuous with respective final via openings 52, 54, in turn forming respective dual damascene openings 57, 59. Final via openings 52, 54 expose underlying portions 78 of metal structure 12 and bottom electrodes 30', 30". Capacitance trench 25 includes sidewalls 50 formed of remaining portions of capacitance dielectric layer 32".